

NPN SILICON TRANSISTOR

FEATURES

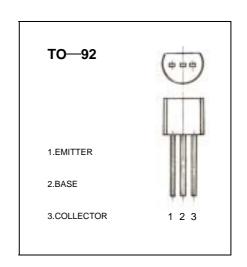
Power dissipation

 P_{CM} : 0.4 W (Tamb=25°C)

Collector current

I_{CM} : 0.1 A

Collector-base voltage



ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	Ic= 100 μ A, I _E =0	50			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	Ic= 0. 1 mA, I _B =0	45			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = 100 μ A, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =50 V , I _E =0			0.1	μА
Collector cut-off current	I _{CEO}	V _{CE} =35 V, I _B =0			0.1	μА
Emitter cut-off current	I _{EBO}	$V_{EB}=$ 3 V , $I_{C}=0$			0.1	μА
DC current gain(note)	H _{FE (1)}	V _{CE} = 5 V, I _C = 1mA	60		1000	
Collector-emitter saturation voltage	V _{CE} (sat)	I _C = 100mA, I _B = 5 mA			0.3	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C = 100 mA, I _B = 5mA			1	V
Transition frequency	f _T	V_{CE} = 5 V, I_{C} = 10mA f =30MHz	150			MHz

CLASSIFICATION OF H_{FE(1)}

	1 =(1)			
Rank	A	В	С	D
Range	60-150	100-300	200-600	400-1000

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